



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C
30V	0.15Ω @ $V_{GS} = 4.5V$		2A
	0.2Ω @ $V_{GS} = 2.5V$	SOT23	1.6A
	0.25Ω @ $V_{GS} = 1.8V$	30123	1.4A
	0.3Ω @ V _{GS} = 1.5V		1.2A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The DMN3300UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

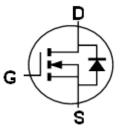
https://www.diodes.com/quality/product-definitions/

Mechanical Data

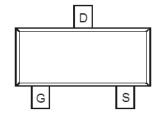
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 <a> ®
- Weight: 0.008 grams (Approximate)







Equivalent Circuit



Top View

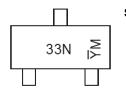
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3300UQ-7	SOT23	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



SOT23

33N = Marking Code $\overline{Y}M$ = Date Code Marking \overline{Y} = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н		J	K	L	М	N	0	Р	R	S	T
	1	1		1	1				1			
				_		_		A	O		NI	D
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	1.5 1.2	А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	2.0 1.6	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	8	Α		
Maximum Body Diode Continuous Current (Note 6)			I _S	1.6	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation	(Note 5)	D	0.7	W	
Total Power Dissipation	(Note 6)	P _D	1.3		
Thermal Resistance, Junction to Ambient	(Note 5)	_	176		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	102	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	$R_{ heta JC}$	45		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

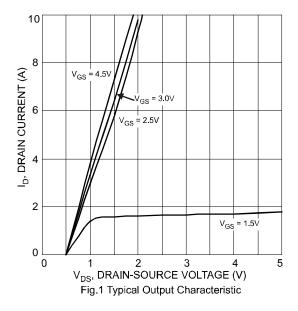
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Symbol	IAIIII	тур	WIGA	Oilit	rest condition	
Drain-Source Breakdown Voltage	BV _{DSS}	30	37	_	V	V _{GS} = 0V, I _D = 100μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 30V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.5		1	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
			100	150		$V_{GS} = 4.5V, I_D = 4.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	140 185 240	200 250 300	mΩ	$V_{GS} = 2.5V, I_D = 3.5A$	
Static Dialit-Source Off-Resistance						$V_{GS} = 1.8V, I_D = 1.5A$	
						$V_{GS} = 1.5V, I_D = 0.5A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.1	V	$V_{GS} = 0V, I_S = 0.5A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		193		рF	101/11/	
Output Capacitance	Coss	_	35	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		23	_	pF	1 = 1.01/11 12	
Turn-On Delay Time	t _{D(ON)}	_	7	_			
Rise Time	t _R	_	24	_	ns	$V_{DD} = 10V$, $R_L = 10\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	24	_	115	$I_D = 1A, V_{GEN} = 4.5V, R_G = 6\Omega$	
Fall Time	t _F	_	12	_			

Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.





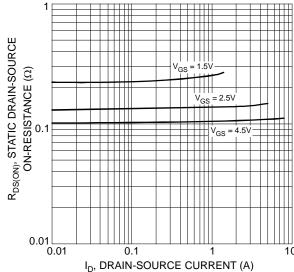


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

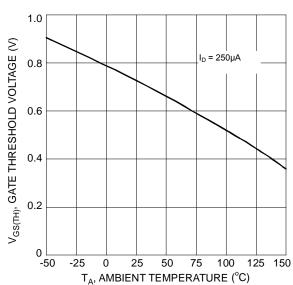
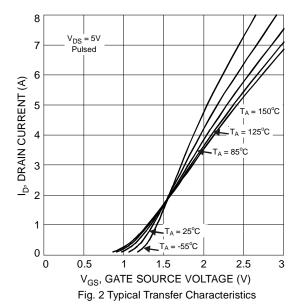


Fig. 5 Gate Threshold Variation vs. Ambient Temperature



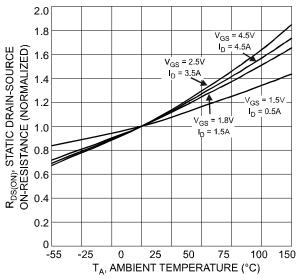
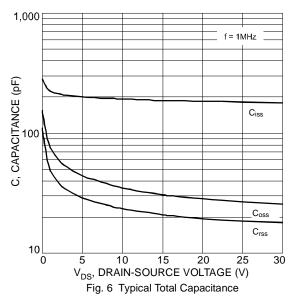
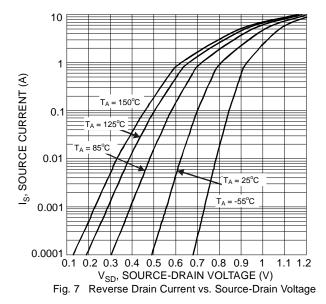
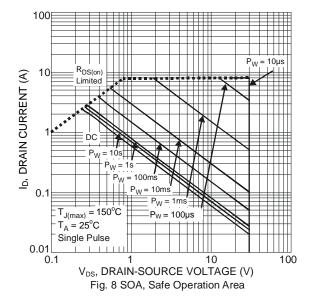


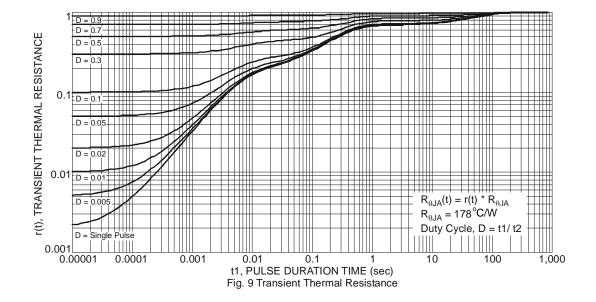
Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature







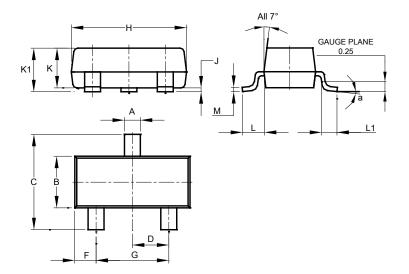






Package Outline Dimensions

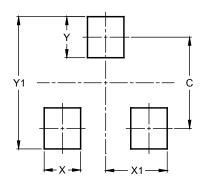
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
٦	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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